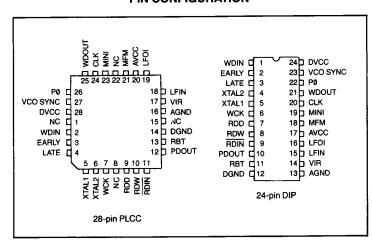
Analog Floppy Disk Data Separator (AFDDS)

FEATURES

- ☐ 1 Mb/s, 750, 500, 300, 250 and 125 Kb/s disk data rates Analog Data Separator performs complete data separation for floppy disk drives. Separates FM or MFM encoded data. 31/2", 51/4" and 8" compatible.
- ☐ No adjustments necessary
- ☐ Provides clock for FDC765A
- ☐ High Performance Dual Gain Analog Phase Locked Loop
- ☐ Variable Write Precompensation
- ☐ Internal Crystal Oscillator
- ☐ 300 Kb/s with clock frequency change and no filter change
- □ On-chip VCO
- ☐ Fabricated in Low Power CMOS
- ☐ TTL Compatible I/O
- ☐ Single + 5V Supply

PIN CONFIGURATION



GENERAL DESCRIPTION

Self Tuning

The FDC92C81 is a high performance CMOS Dual Gain Analog Floppy Disk Data Separator (AFDDS). The FDC92C81 is compatible with 3.5", 5.25" and 8" floppy disk drives, and provides all clocks required by the industry standard FDC765A and FDC72C65 floppy disk controllers.

The FDC92C81 incorporates all the active components necessary to implement analog floppy disk data separation, eliminating the need for discrete transistors. Only a crystal

and a few external resistors and capacitors are required. Using the FDC92C81 and a floppy disk controller chip, a system designer can build a highly reliable, cost efficient double or single density floppy disk subsystem requiring no tuning adjustments.

Three different user selectable values for write precompensation assure reliable positioning of data when writing to disk.

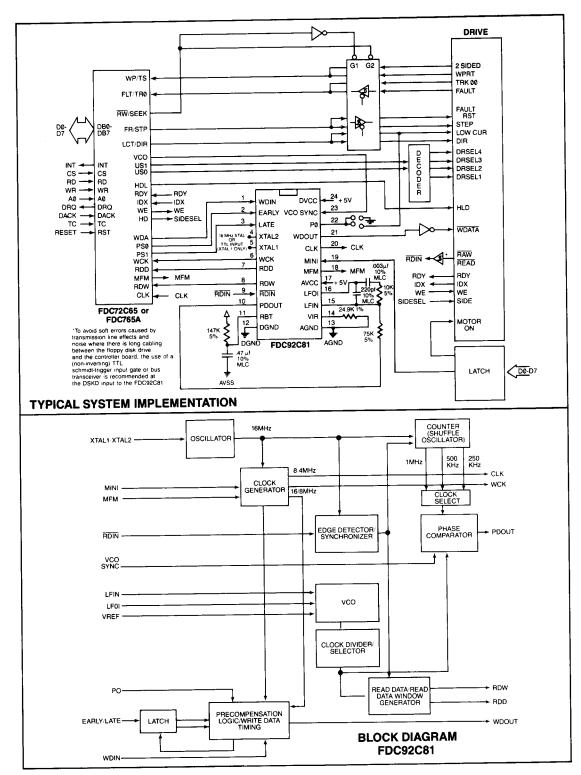


TABLE 1—FDC92C81 DESCRIPTION OF PIN FUNCTIONS

PIN NO.	NAME	SYMBOL	I/O	DESCRIPTION
PIN NO.	Write Data In	WDIN	"0	This input contains the serial clock and data bits which may
				be precompensated and output to the drive.
2	Early	EARLY		Used for precompensation. When high, the write data bit will be written early. Refer to table below.
3	Late	LATE		Used for precompensation. When high, the write data bit will be written late.
				EARLY LATE PULSE POSITION
				0 0 nominal
				1 0 early 0 1 late
				1 1 not used
4	Crystal	XTAL2	O	A 16.000 MHz parallel resonant crystal may be connected
5	Crystal	XTAL1	'	between XTAL1 and XTAL2. If a TTL signal is used in place of a crystal, the signal should be connected to XTAL1 while XTAL2 is left unconnected.
6	Write Clock	WCK	0	This output contains the clock which controls the rate at which data is written to the drive. See table for MINI pin.
7	Read Data	RDD	0	This output contains the reclocked encoded bit stream from the drive.
8	Read Data Window	RDW	0	This output is a function of the internal VCO frequency which tracks and properly frames the encoded drive bit stream for reliable clocking into the floppy disk controller.
9	Read Data In	RDIN	ı	This input is the read data from the floppy disk drive. The input is active low. The leading edge (high to low transition) is used for all frequency tracking operations.
10	Phase Detect Out	PDOUT	0	The output of the phase detect circuit. A 75K 5% resistor is connected between this output and LFIN.
11	Bias Reference	RBT	l	An external 147K 5% resistor connected between this pin and AVCC establishes a bias reference current for the VCO. This input should not be forced low.
12	Digital Ground	DGND		Digital Ground
13	Analog Ground	AGND	<u> </u>	Analog Ground
14	Voltage to Current Reference	VIR	ı	A 24.9K 1% metal film resistor connected between this pin and AVSS establishes a current reference for the on-chip voltage to current converter which is part of the VCO.
15	Low-pass Filter In	LFIN	ı	This is the input to the low pass filter amplifier. A resistor is connected between this input and PDOUT and a low pass filter is connected between this input and LFOI.
16	Low-pass Filter	LFOI	I/O	This pin is the output of the low pass filter amplifier and the input to the VCO.
17	Analog Vcc	AVCC		+5V analog power supply
18	MFM Mode	MFM	ı	When this input is high, the chip is in MFM mode. When low, the chip is in the FM mode.
19	MINI	MINI	i	This input, along with the input P0 specifies the amount of precompensation to be used. See table for the P0 pin. This input along with MFM controls the CLK and WCK outputs.
				MFM MINI WCK CLK
				0 0 500KHz 8MHz 0 1 250KHz 4MHz
				0 1 250KHz 4MHz 1 0 1MHz 8MHz
				1 1 500KHz 4MHz
20	Clock	CLK	0	This output is a 4MHz or 8MHz clock. See table above.
21	Write Data Out	WDOUT	0	This output is the precompensated serial write data to the floppy disk drive.

TABLE 1—FDC92C81 DESCRIPTION OF PIN FUNCTIONS CONTINUED

PIN NO.	NAME	SYMBOL	1/0		DESCRIPT	
22	Precompensation	P0	i	This input along with the MINI input specifies the amount precompensation to be used.		
				MINI	PO	PRECOMP
				0	0	0.0ns
				l ő	1	62.5ns
	1		1	1	0	0.0ns
			1	1	1	125.0ns
23	VCO Sync	VCO SYNC	1	VCO locks to cl	ock when low and	to data when high.
24	Digital Vcc	DVCC		+ 5V digital pov	wer supply.	

MODE GAIN IMPLEMENTATION

The phase locked loop gain of the FDC92C81 is controlled by switching between two modes of operation, shuffle oscillator and arm on data. The mode change is via VCO SYNC. The shuffle oscillator mode is considered the high gain mode and the arm on data mode is considered the low gain mode.

Arm On Data Mode

The purpose of the arm on data mode is to reduce the gain so that the chip can handle higher amounts of bit jitter. In this mode, each code bit received from the drive resets the phase compare circuits and a counter (shuffle oscillator). The phase compare circuits are only armed for one compare cycle after each code bit. The counter is set such that ½ bit cell after the phase compare reset has gone away, it creates an edge. (Only one compare is performed until the next code bit is received.) This edge is compared against the edges of the VCO by the phase compare circuits. The relationship between these edges is used to generate one pump-up or

pump-down signal. Therefore, in this mode, each code bit causes only one update to the loop.

Shuffle Oscillator Mode

The shuffle oscillator mode allows for a fast lock to data time when attempting to acquire data synchronization. In this mode, each code bit received from the drive resets the phase compare circuits and a counter (shuffle oscillator). The phase compare circuits are always armed. The counter is set such that ½ bit cell after the phase compare reset has gone away, it creates an edge. Each ½ bit cell thereafter creates an edge until reset by another code bit. This edge is compared against the edges of the VCO by the phase compare circuits. The relationship between these edges is used to generate pump-up/pump-down signals. In MFM codes, the minimum spacing between code bits is one bit cell, the maximum spacing is two bit cells. Therefore, in this mode, each code bit can cause up to four updates to the loop. This is how the gain of the loop is increased.

TYPICAL PERFORMANCE SPECIFICATIONS

PARAMETER	500KHz	300KHz	250KHz	UNITS
Bit Jitter Nominal Speed + 5% Speed - 5% Speed	380 360 380	620 600 660	760 740 840	nsec nsec nsec
Window Margin Early Late	480 400	800 720	860 820	nsec nsec

Lock to Encoded Data	less than 3 bytes
LOCK TO ELICOGED Data	

ELECTRICAL CHARACTERISTICS

MAXIMUM GUARANTEED RATINGS

Operating Temperature Range	0°C to +70°C
Storage Temperature Range	55°C to +150°C
Lead Temperature (soldering, 10 sec.)	
Positive Voltage on any Pin, with respect to Ground	
Negative Voltage on any Pin, with respect to Ground	
Power Dissipation	0.25W
Positive Voltage on V _{cc} Pin, with respect to Ground	7.0V

Stresses above those listed may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or at any other condition above those indicated in the operational sections of this specification is not implied.

NOTE: When powering this device from laboratory or system power supplies, it is important that the "Maximum Guaranteed Ratings" not be exceeded, or device failure can result. Some power supplies exhibit voltage spikes or "glitches" on their outputs when AC power is switched off. In addition, voltage transients on the AC power supply line may appear on the DC output. If this possibility exists it is suggested that a clamp circuit be used.

DC ELECTRICAL CHARACTERISTICS TA = 0°C to 70°C, V_{cc} = 5.0V ±5% unless otherwij

PARAMETERS	MIN	TYP	MAX	UNITS	COMMENT Some parametric first a frest specific
INPUT VOLTAGE					COMMETO Same parameter from the second secon
High Level V _⊩ High Level V _∺	-0.3 2.0		0.8 (VCC)	V	
INPUT VOLTAGE Low level V _{IL} High Level V _{IH}	-0.3 3.2		0.8 (VCC)	V	XTAL 1, XTAL 2
OUTPUT VOLTAGE Low Level V _{oL} High Level V _{oH}	2.4		0.4	v v	CLK, WCK, RDD, RDW, MFM, MINI, WDOUT Io. = 1.6mA except CLK IoL = 0.4mA, CLK only IoH = -100uA except CLK IOH = -400uA, CLK only
POWER SUPPLY CURRENT			TBD	mA	
INPUT LEAKAGE CURRENT			TBD	uA	$V_{IN} = 0$ to V_{CC}
INPUT CAPACITANCE C _{IN}		TBD		pF	WDIN, EARLY, LATE, RDIN, PØ, SYNC, XTAL 1

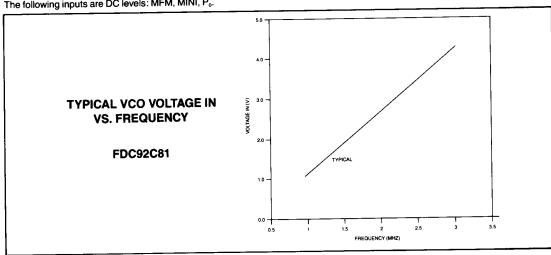
AC ELECTRICAL CHARACTERISTICS TA = 0°C to 70°C, V_{cc} = 5.0V ±5% unless otherw

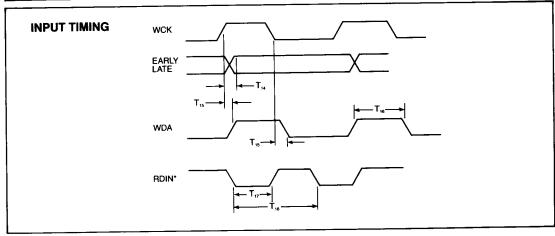
PARAMETERS	SMBL	MIN	TYP	MAX	UNIT	LOAL	Some Description in not a final
Read data width	T,	40			ns	20pf	A STATE OF THE PARTY OF THE PAR
Window setup time	T ₂	15			ns	20pf	
Window hold time	T ₃	15			ns	20pf	
Window cycle time	T,	-	2 1 4 2		us us us us	20pf	MFM = 0 MINI = 0 MFM = 1 MINI = 0 MFM = 0 MINI = 1 MFM = 1 MINI = 1
WCK high	T ₅	80	250	350	ns	20pf	
WCK cycle time	T _e		4 2 1		us us us	20pf 20pf 20pf	125KHz data rate 250KHz data rate 500KHz data rate
CLK high	T,	40			ns	20pf	
CLK low	Ta	40			ns	20pf	
CLK period	T,	120		500	ns	20pf	
WDOUT width	T _{9a}	250	315	350	us	20pf	x2 if mini = 1
CLK ↑ to WCK ↑ delay	T ₁₀	0		40	ns		

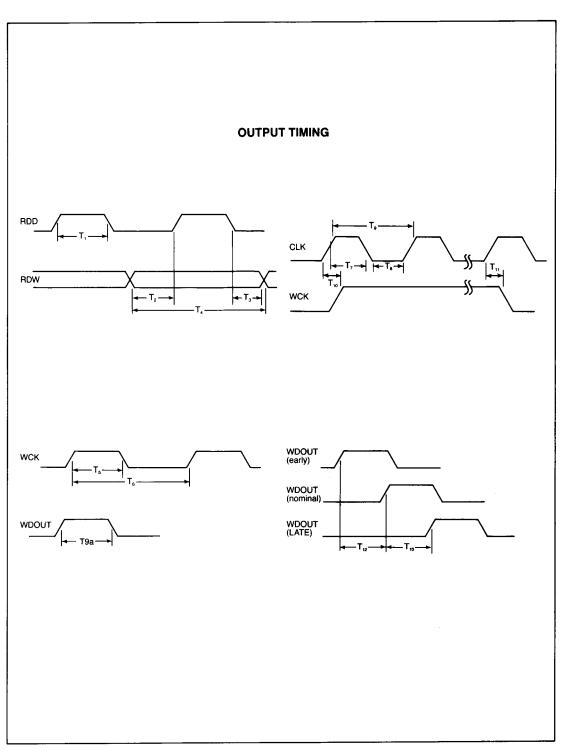
AC ELECTRICAL CHARACTERISTICS CONTINUED

PARAMETERS	SMBL	MIN	TYP	MAX	UNIT	LOAD	COmment Subject to Charge.
CLK ↑ to WCK ↓ delay	T,,	0		40	ns		
WDOUT early rising edge to WDOUT nom. rising edge	T ₁₂	Desired Precomp Value			see table for pin 22		
WDOUT nom. rising edge to WDOUT late rising edge	T ₁₃		Desired Precomp Value			see table for pin 22	
Pre-shift delay time from WCK positive edge	T,4	20		100	ns		
WDIN delay time rising edge of WCK to rising edge of WDIN, falling edge of WCK to falling edge of WDIN	T ₁₅	20		100	ns		
WDIN width	T ₁₆	30	200	300	ns	<u> </u>	
Read data width	T ₁₇	100			ns		
Read data cycle time	T ₁₈		2 2 4 4		us us us us		500 Kb/s MFM, 250 Kb/s FM 250 Kb/s MFM, 125 Kb/s FM

The following inputs are DC levels: MFM, MINI, Po.

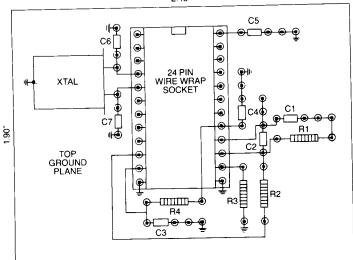






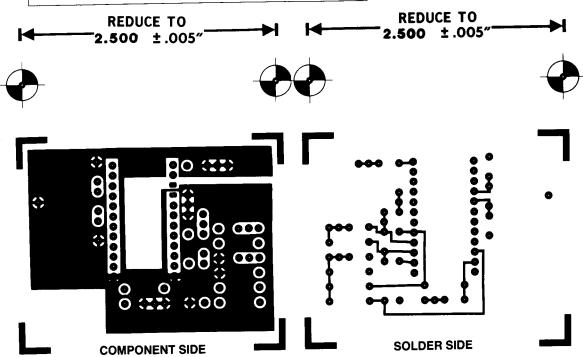
NOTE: For an updated data sheet please fill out the reply card in the back of this catalog or call SMC at (516) 273-3100.





RESISTOR VALUES				
R1	10K 5%			
R2	75K 5%			
R3	24.9K 1% metal film			
R4	147K 5%			

CAPACITOR VALUES					
C1	.003 uf 10% MLC				
C2	220 pf 10% MLC				
C3	47 uf 10% MLC				
C4	.22 uf 10%				
C5	.22 uf 10%				
C6	60 pf 10%				
C7	60 pf 10%				



NOTE: The printed circuit board artwork shown above is included for illustration only. Camera ready artwork is available through your SMC representative or regional sales office.

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